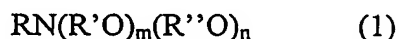


## Claims:

1. A slurry composition for secondary polishing of semiconductor wafers comprising 2~10% by weight of colloidal silica having an average particle diameter of 30~80nm as an abrasive, 0.5~1.5% by weight of ammonia, 0.2~1% by weight of a hydroxyalkylcellulose-based water-soluble polymeric thickener, 0.03~0.5% by weight of a polyoxyethylenealkylamine ether-based nonionic surfactant, 0.01~1% by weight of a quaternary ammonium base and the balance of deionized water.

2. The slurry composition according to claim 1, wherein the colloidal silica has a first particle diameter of 35~50nm and a second particle diameter of 60~80nm.

3. The slurry composition according to claim 1, wherein the polyoxyethylenealkylamine ether-based nonionic surfactant is represented by the following formula 1:



wherein R is an alkyl group having 1~3 carbon atoms, R' and R'' are each independently ethylene or isopropylene group, m and n are each independently an integer of from 10 to 80, and m + n is within the range of 20~90.

4. The slurry composition according to claim 1, wherein the water-soluble polymeric thickener is a material selected from the group consisting of hydroxypropylcellulose, hydroxybutylmethylcellulose, hydroxypropylmethylcellulose, hydroxyethylcellulose, lipophilically-modified hydroxyethylcellulose, hydroxymethylcellulose and methylcellulose, and has a weight average molecular weight of 100,000~1,500,000.

5. The slurry composition according to claim 1, wherein the water-soluble polymeric thickener is included to adjust the viscosity of the slurry at 7~80cP.

6. The slurry composition according to claim 1, wherein the quaternary ammonium base is a material selected from the group consisting of tetramethylammonium hydroxide, tetraethylammonium hydroxide, trimethylethoxyammonium hydroxide and N,N-dimethylpiperidine hydroxide.